1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5330PA.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
I _C	collector current		-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	75	100	mΩ



30 V, 3 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view DFN2020-3 (SOT1061)	2 sym021

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PBSS4330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4330PA	AH

30 V, 3 A NPN low VCEsat (BISS) transistor

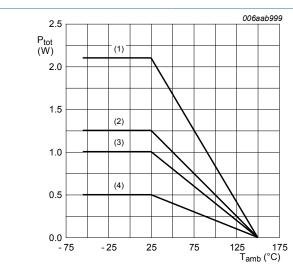
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	30	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	Α
I _B	base current			-	500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al_2O_3 , standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

PBSS4330PA

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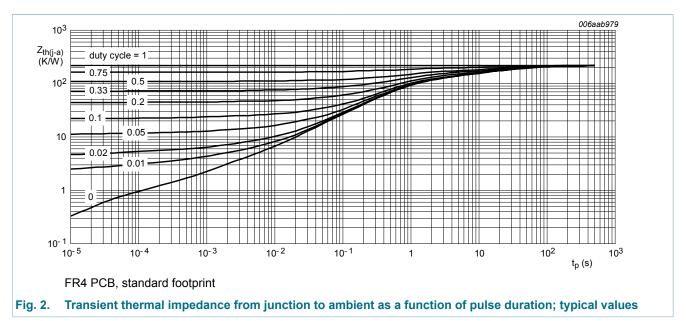
30 V, 3 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient			[1]	-	-	250	K/W
			[2]	-	-	125	K/W
	ambient		[3]	-	-	100	K/W
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



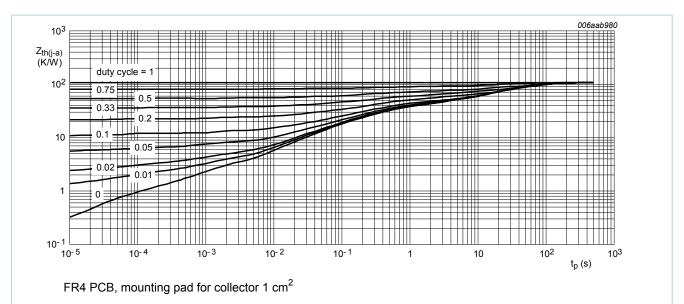


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

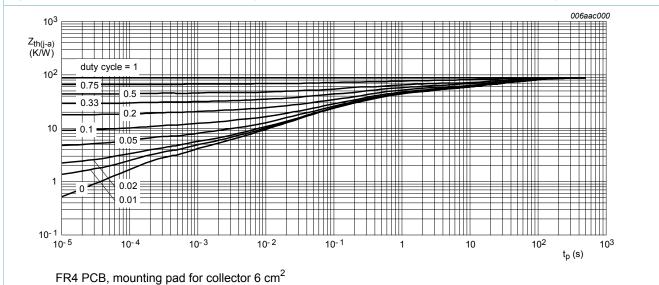
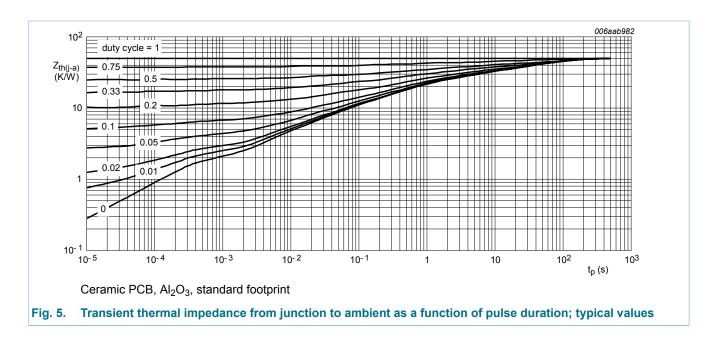


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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10. Characteristics

Table 7. Characteristics

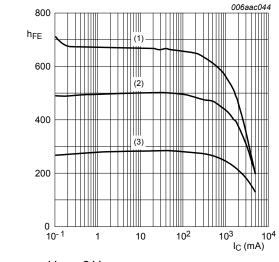
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V_{CB} = 30 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 24 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
l _{ЕВО}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 0.5 \text{ A}; \text{ pulsed};$ $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	300	465	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	270	435	700	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	230	370	-	
		V_{CE} = 2 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	180	310	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = 0.5 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	40	60	mV
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	80	110	mV
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	155	220	mV
		I_C = 3 A; I_B = 300 mA; pulsed;	-	220	300	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb} = 25 \ ^{\circ}C$	-	75	100	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.95	1.1	V
		$I_C = 3 \text{ A}; I_B = 300 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	1.07	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	0.76	1	V
t _d	delay time	V _{CC} = 9 V; I _C = 2 A; I _{Bon} = 0.1 A;	-	11	-	ns
t _r	rise time	I_{Boff} = -0.1 A; T_{amb} = 25 °C	-	52	-	ns
t _{on}	turn-on time		-	63	-	ns
ts	storage time		-	230	-	ns
f	fall time		-	40	-	ns
off	turn-off time		-	270	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	210	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	21	30	pF



 $V_{CE} = 2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 6. DC current gain as a function of collector current; typical values

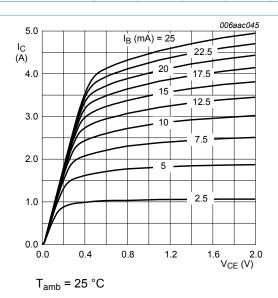
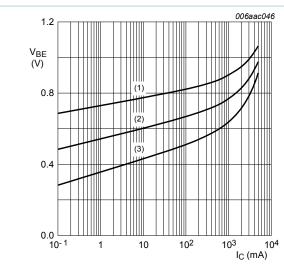


Fig. 7. Collector current as a function of collectoremitter voltage; typical values



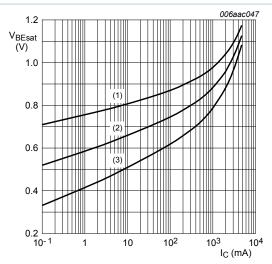
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter voltage as a function of collector current; typical values



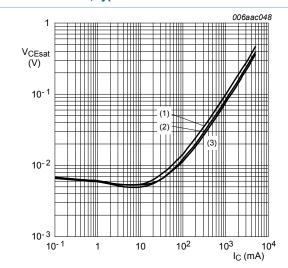
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



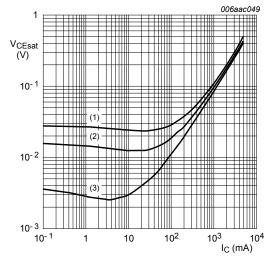
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

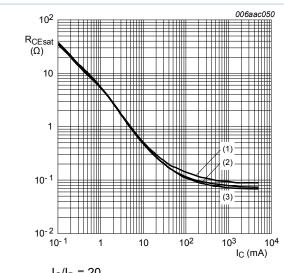


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



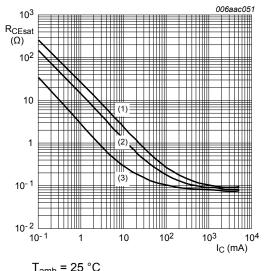
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

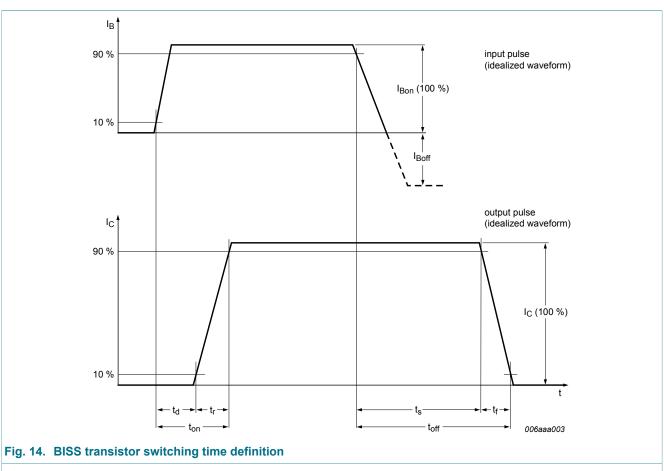
(2)
$$I_{\rm C}/I_{\rm B} = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



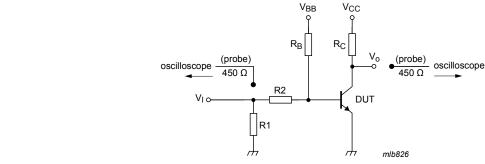
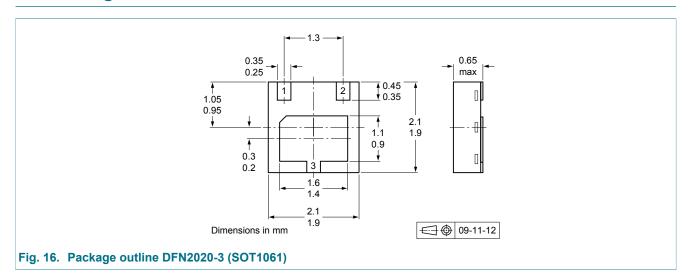


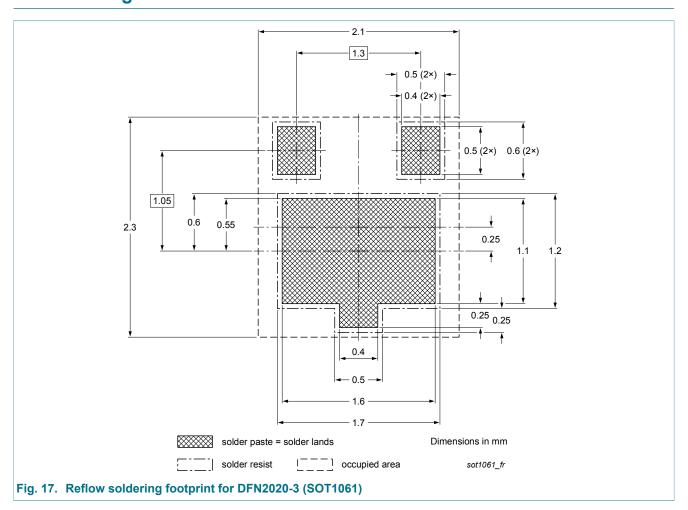
Fig. 15. Test circuit for switching times

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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4330PA v.2	20150407	Product data sheet	-	PBSS4330PA v.1		
Modifications:	 Condition V_{CE} changed for parameter I_{CES} in Table 7, Characteristics 					
PBSS4330PA v.1	20100419	Product data sheet	-	-		

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